



10N60Z-Q

Preliminary

Power MOSFET

10A, 600V N-CHANNEL POWER MOSFET

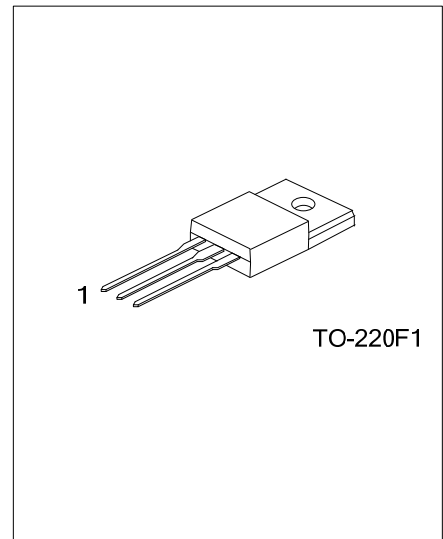
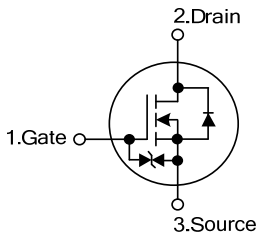
DESCRIPTION

The **UTC 10N60Z-Q** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 0.8\Omega @ V_{GS} = 10V$
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability

SYMBOL



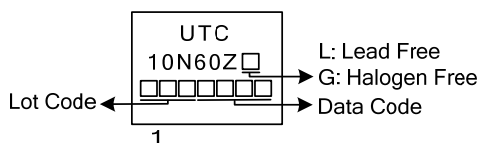
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N60ZL-TF1-T	10N60ZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N60ZL-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 20	V
Avalanche Current (Note 2)		I_{AR}	10	A
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	38	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	445	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 8.9\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$ Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 9.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.5	$^{\circ}\text{C}/\text{W}$

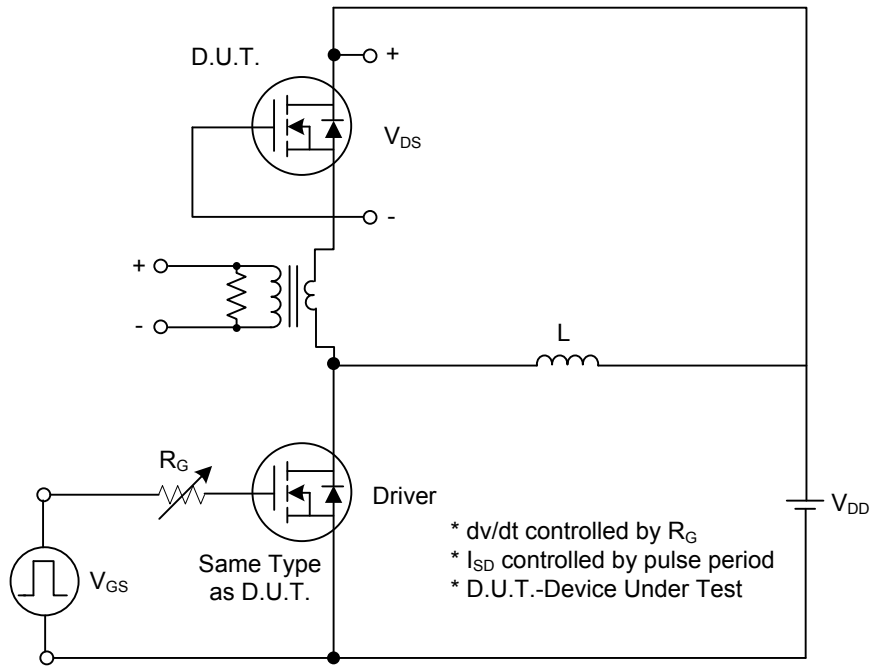
■ ELECTRICAL CHARACTERISTICS($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$			1	μA
Gate-Source Leakage Current	Forward	I_{GSS} $V_{GS}=20V, V_{DS}=0V$ $V_{GS}=-20V, V_{DS}=0V$			5	μA
	Reverse				-5	μA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, Referenced to 25°C		0.7		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$		0.7	0.8	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{ MHz}$		790	1020	pF
Output Capacitance	C_{OSS}			139	180	pF
Reverse Transfer Capacitance	C_{RSS}			22	28	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DS}=30V, I_D=0.5A,$ $R_G=25\Omega$ (Note 1, 2)		56	70	ns
Turn-On Rise Time	t_R			110	170	ns
Turn-Off Delay Time	$t_{D(OFF)}$			300	360	ns
Turn-Off Fall Time	t_F			160	240	ns
Total Gate Charge	Q_G	$V_{DS}=50V, I_D=1.3A,$ $V_{GS}=10V$ (Note 1, 2)		43	56	nC
Gate-Source Charge	Q_{GS}			7		nC
Gate-Drain Charge	Q_{GD}			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				38	A

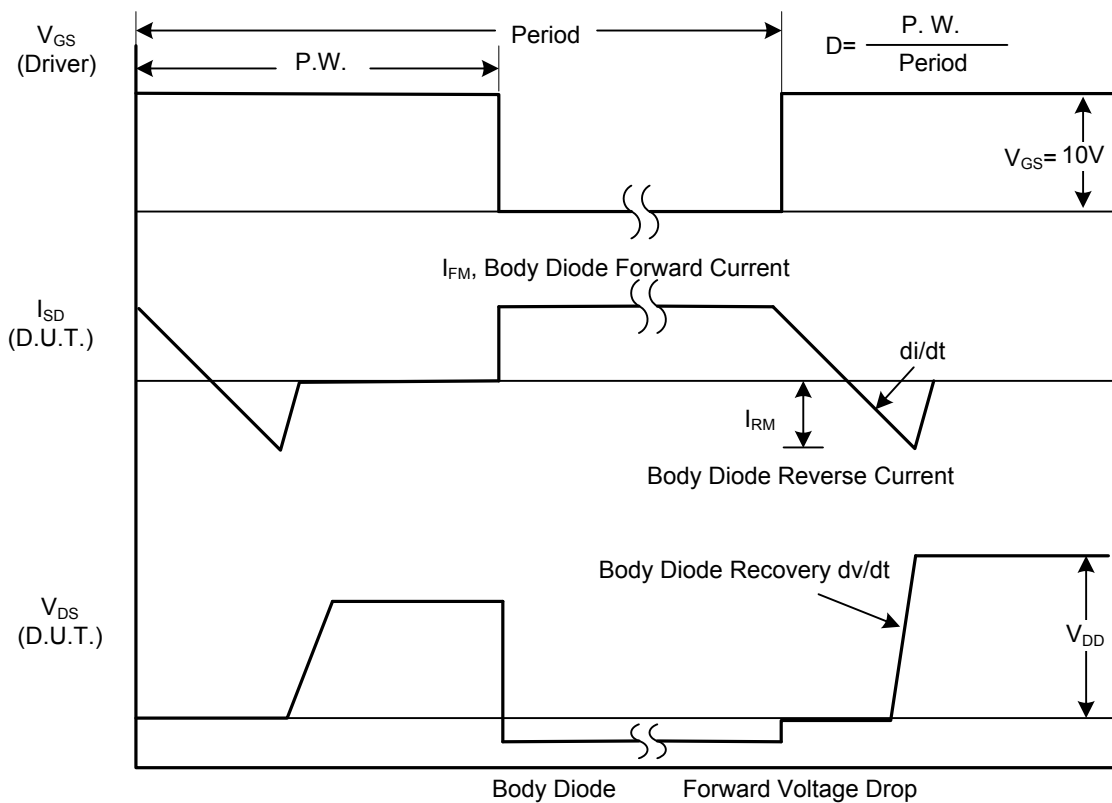
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

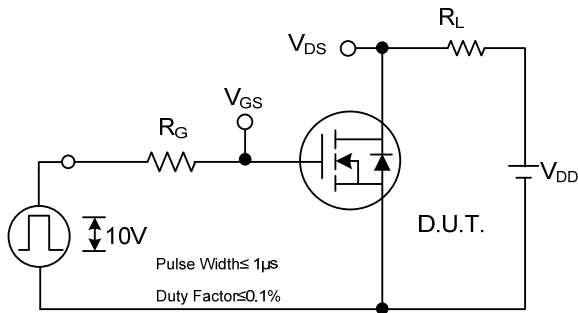


Peak Diode Recovery dv/dt Test Circuit

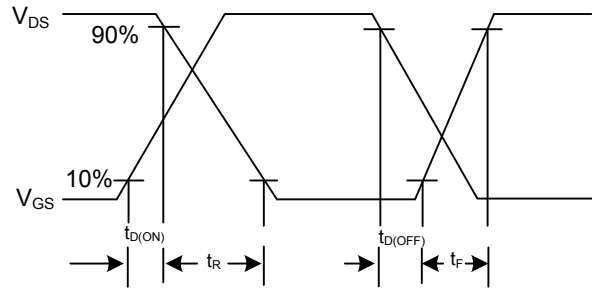


Peak Diode Recovery dv/dt Waveforms

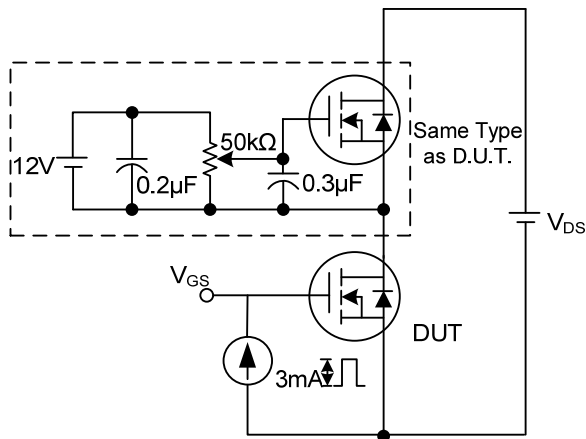
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



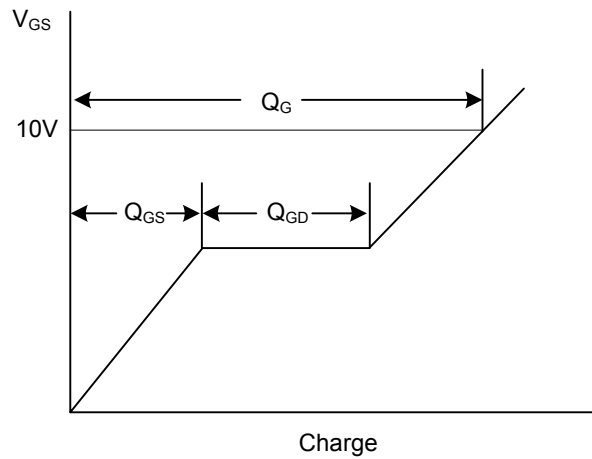
Switching Test Circuit



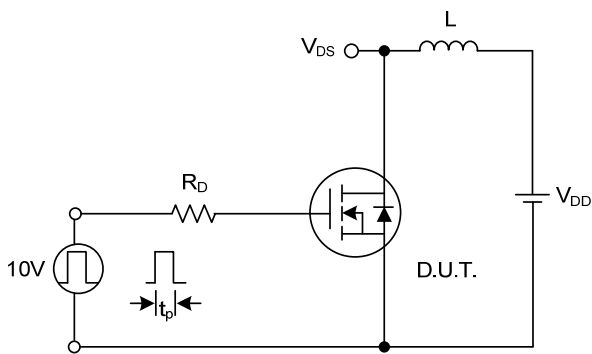
Switching Waveforms



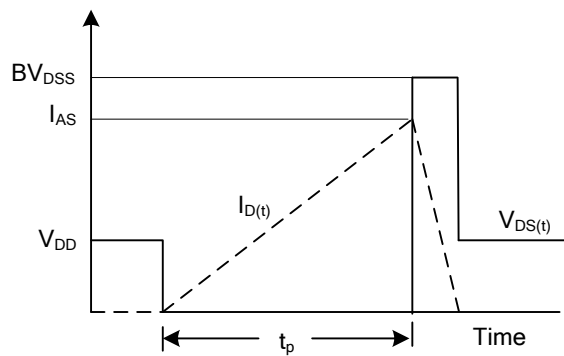
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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